NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TVV020** is Designed for Television Band III Applications up to 225 MHz.

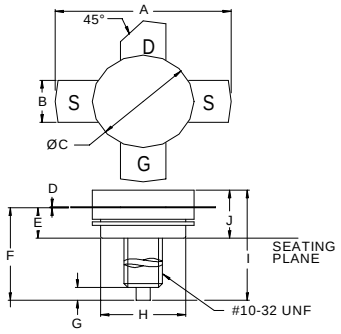
FEATURES:

- Common Emitter
- P_G = 8.0 dB at 20 W/225 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	8.0 A
V_{CEO}	35 V
V_{CES}	60 V
V_{EBO}	4.0 V
P_{DISS}	140 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.5 °C/W

PACKAGE STYLE .500 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.050 / 26.67
B	.220 / 5.59	.230 / 5.84
C	.495 / 12.57	.505 / 12.83
D	.003 / 0.08	.007 / 0.18
E	.160 / 4.06	.180 / 4.57
F	.622 / 15.80	
G	.100 / 2.54	.130 / 3.31
H	.415 / 10.54	.425 / 10.80
I	.720 / 18.29	
J	.250 / 6.35	.290 / 7.37

ORDER CODE: ASI10659

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 50 mA	65			V
BV_{CER}	I_C = 50 mA R_{BE} = 10 Ω	60			V
BV_{CEO}	I_C = 50 mA	35			V
BV_{EBO}	I_E = 10 mA	4.0			V
I_{CES}	V_{CB} = 50 V			5.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 1.0 A	20		120	---
C_{OB}	V_{CB} = 30 V f = 1.0 MHz			85	pF
P_G	V_{CE} = 25 V I_C = 2.5 A f = 225 MHz	8.0			dB
IMD_3	P_{OUT} = 20 W	-51			dBc